

ZXMN6A25K 60V DPAK N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$ $R_{DS(on)}(\Omega)$		I _D (A)
60	0.050 @ V _{GS} = 10V	10.7
00	0.070 @ V _{GS} = 4.5V	9



Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Features

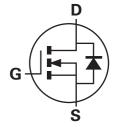
- · Low on-resistance
- · Fast switching speed
- · Low gate drive
- DPAK package

Applications

- · DC-DC converters
- · Power management functions
- · Disconnect switches
- · Motor control

Ordering information

Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZXMN6A25KTC	13	16	2,500



G S Pinout - top view

Device marking

ZXMN 6A25

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DSS}	60	V
Gate-source voltage	V _{GS}	±20	V
Continuous drain current @ V _{GS} = 10V; T _{amb} =25°C ^(b)	I _D	10.7	Α
@ V _{GS} = 10V; T _{amb} =70°C ^(b)		8.6	Α
@ V _{GS} = 10V; T _{amb} =25°C ^(a)		7	Α
Pulsed drain current ^(c)	I _{DM}	36	Α
Continuous source current (body diode) ^(b)	I _S	11.8	Α
Pulsed source current (body diode) ^(c)	I _{SM}	36	Α
Power dissipation at T _{amb} =25°C ^(a)	P _D	4.25	W
Linear derating factor		34	mW/°C
Power dissipation at T _{amb} =25°C ^(b)	P _D	9.85	W
Linear derating factor		78.7	mW/°C
Power dissipation at T _{amb} =25°C ^(d)	P _D	2.11	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	29.4	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	12.7	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	59.1	°C/W

NOTES:

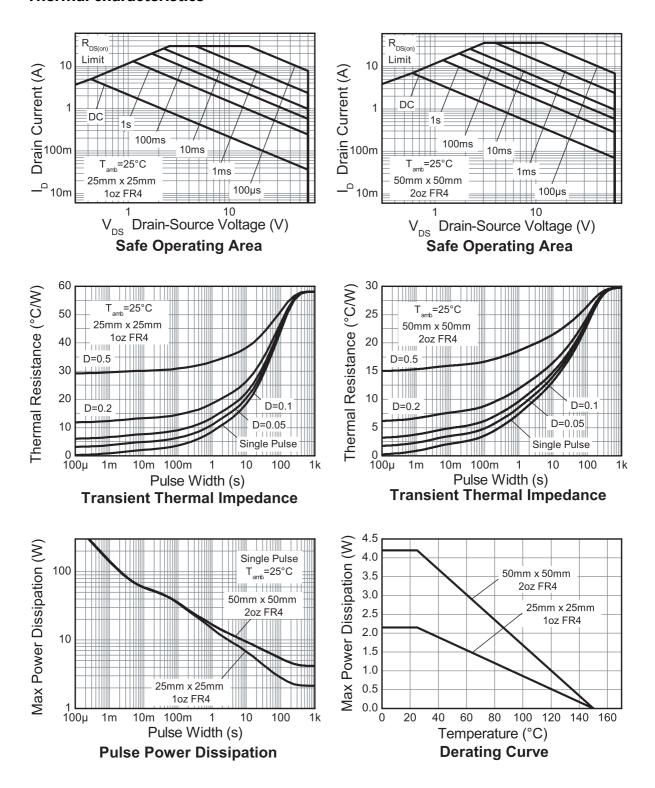
⁽a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

⁽b) For a device surface mounted on FR4 PCB measured at t \leq 10 sec.

⁽c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300 μ s - pulse width limited by maximum junction temperature.

⁽d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz. copper, in still air conditions.

Thermal characteristics



Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Static		I.	l			1
Drain-source breakdown voltage	V _{(BR)DSS}	60			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			1.0	μΑ	V _{DS} = 60V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	1		3	V	I _D = 250μA, V _{DS} =V _{GS}
Static drain-source on-state	R _{DS(on)}			0.050	Ω	V _{GS} = 10V, I _D = 3.6A
resistance ^(*)				0.070	Ω	$V_{GS} = 4.5V, I_D = 3.0A$
Forward transconductance (*)(‡)	9 _{fs}		10.2		S	V _{DS} = 15V, I _D = 4.5A
Dynamic ^(‡)		I.	I			
Input capacitance	C _{iss}		1063		pF	V _{DS} = 30V, V _{GS} =0V
Output capacitance	C _{oss}		104		pF	f=1MHz
Reverse transfer capacitance	C _{rss}		64		рF	
Switching (†) (‡)			!	•		
Turn-on-delay time	t _{d(on)}		3.8		ns	V _{DD} = 30V, I _D = 1A
Rise time	t _r		4.0		ns	R _G ≅6.0Ω, V _{GS} = 10V
Turn-off delay time	t _{d(off)}		26.2		ns	
Fall time	t _f		10.6		ns	
Gate charge	Q_g		11.0		nC	V _{DS} = 30V, V _{GS} = 5V I _D = 1.4A
Total gate charge	Qg		20.4		nC	V _{DS} = 30V, V _{GS} = 10V
Gate-source charge	Q _{gs}		4.1		nC	I _D = 1.4A
Gate drain charge	Q_{gd}		5.1		nC	
Source-drain diode		•		•		
Diode forward voltage ^(*)	V _{SD}		0.85	0.95	V	T _j =25°C, I _S = 5.5A, V _{GS} =0V
Reverse recovery time ^(‡)	t _{rr}		22.0		ns	T _j =25°C, I _S = 2.2A,
Reverse recovery charge ^(‡)	Q _{rr}		21.4		nC	di/dt=100A/μs

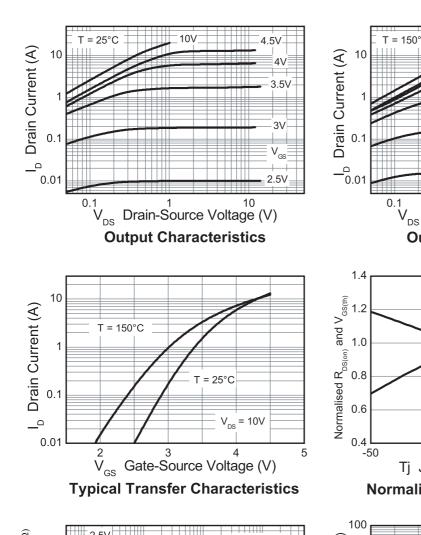
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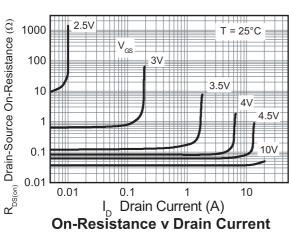
^(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

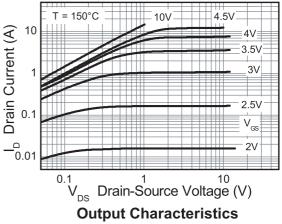
^(†) Switching characteristics are independent of operating junction temperature

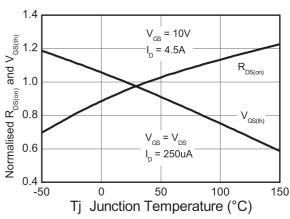
^(‡) For design aid only, not subject to production testing.

Typical characteristics

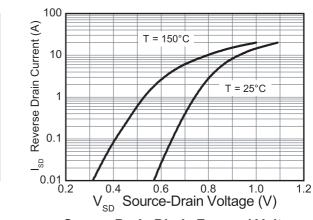








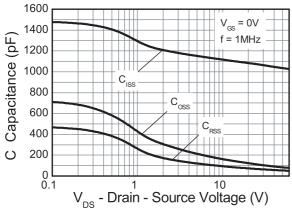
Normalised Curves v Temperature



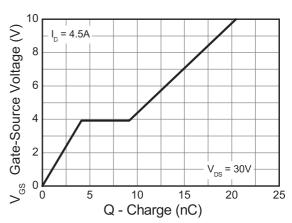
Source-Drain Diode Forward Voltage

ZXMN6A25K

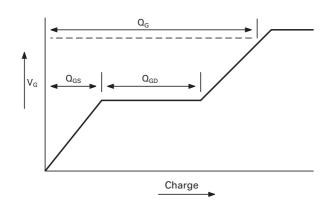
Typical characteristics



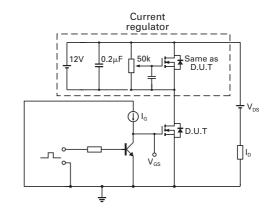
Capacitance v Drain-Source Voltage



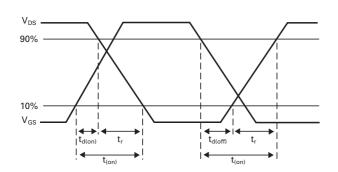
Gate-Source Voltage v Gate Charge



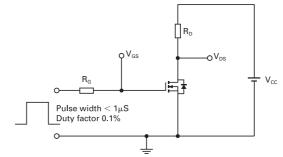
Basic gate charge waveform



Gate charge test circuit



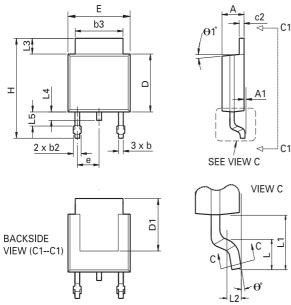
Switching time waveforms



Switching time test circuit

ZXMN6A25K

Package outline - DPAK



<u></u>									
DIM	Inc	hes	Millin	neters	DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
Е	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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